



SOD-323 Schottky Barrier Diode 肖特基势垒二极管

Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	RB751V-40
Pin 管脚	
Mark 打标	

Absolute Maximum Ratings 最大额定值

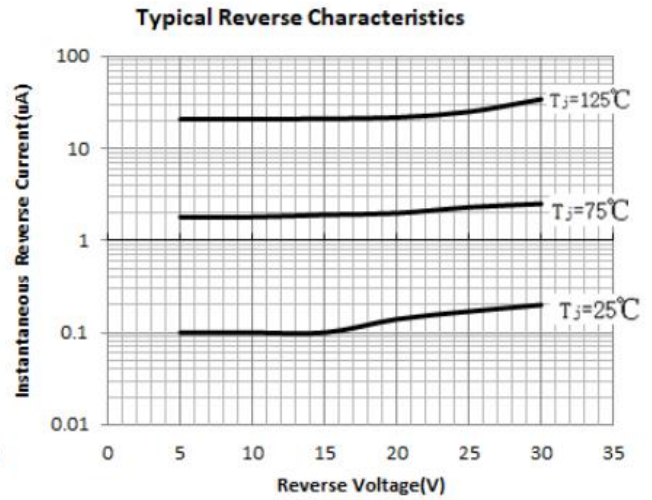
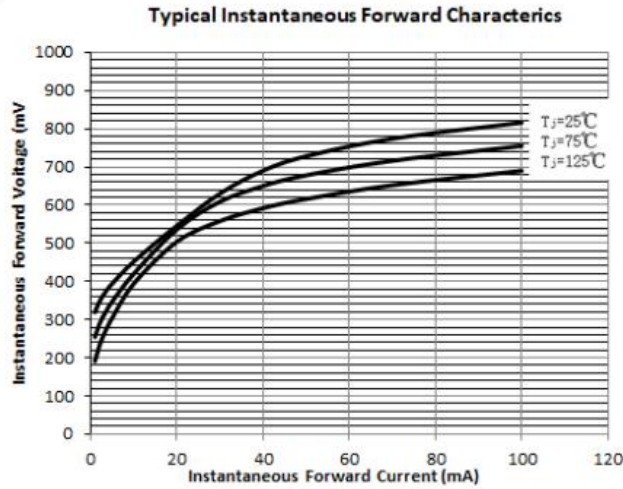
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RM}	40	V
DC Reverse Voltage 直流反向电压	V_R	30	
Forward Work Current 正向工作电流	I_o	30	mA
Peak Forward Surge Current 正向峰值浪涌电流	I_{FSM}	200	mA
Power dissipation 耗散功率	$P_D(T_a=25^\circ C)$	200	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	500	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+125 $^\circ C$	

Electrical Characteristics 电特性

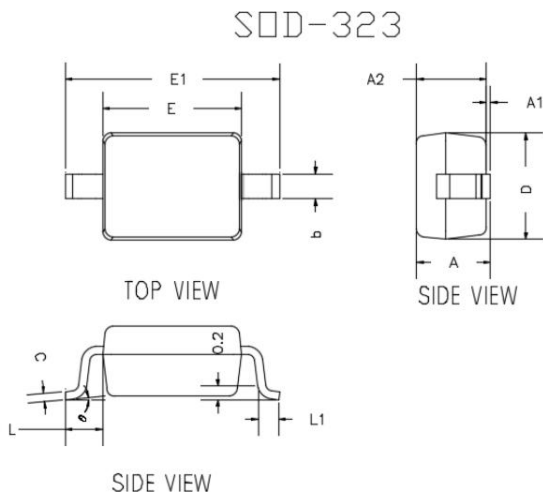
($T_A=25^\circ C$ unless otherwise noted 如无特殊说明, 温度为 25 $^\circ C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=0.1mA$)	$V_{(BR)}$	40	—	V
Reverse Leakage Current 反向漏电流($V_R=30V$)	I_R	—	0.5	μA
Forward Voltage 正向电压($I_F=1mA$)	V_F	—	0.37	V
Diode Capacitance 二极管电容($V_R=1V, f=1MHz$)	C_D	—	10	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	5	nS

■ Typical Characteristic Curve 典型特性曲线



■ Dimension 外形封装尺寸



DIMENSIONS				
DIM	INCHES		MM	
	MIN	MAX	MIN	MAX
A	---	0.0393	---	1.0000
A1	0.0000	0.0039	0.0000	0.1000
A2	0.0314	0.0354	0.8000	0.9000
b	0.0098	0.0157	0.2500	0.4000
c	0.0031	0.0059	0.0800	0.1500
D	0.0472	0.0551	1.2000	1.4000
E	0.0629	0.0709	1.6000	1.8000
E1	0.0984	0.1063	2.5000	2.7000
L	0.0187TYP		0.475TYP	
L1	0.0098	0.0157	0.250	0.400
θ	0°	8°	0°	8°